

### INCHANGE SEMICONDUCTOR

### **isc Silicon NPN Power Transistor**

# KSD1691

#### DESCRIPTION

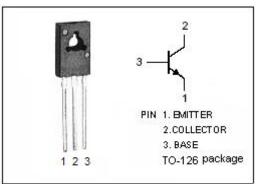
- High Collector Current -I<sub>C</sub>= 5A
- Low Collector Saturation Voltage
- : V<sub>CE(sat)</sub>= 0.3V(Max.)@ I<sub>C</sub>= 2A
- Complement to Type KSB1151
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

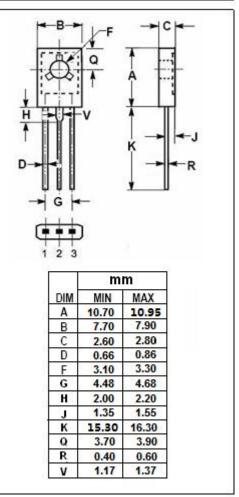
### APPLICATIONS

• Designed for use in DC-DC converter, or driver of solenoid or motor.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)				
SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V	
$V_{\text{EBO}}$	Emitter-Base Voltage	7	V	
lc	Collector Current-Continuous	5	A	
I <sub>CP</sub>	Collector Current-Pulse	8	A	
I <sub>B</sub>	Base Current-Continuous	1	A	
5	Collector Power Dissipation @ $T_c$ =25°C	20	W	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.3		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	

## ADOOLUTE MAXIMUM DATINGO/T -2500





1



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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	мах	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			0.3	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB}$ = 50V; I <sub>E</sub> = 0			10	μA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			10	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 1V	60			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 1V	100		400	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 1V	50			

Switching Times

t <sub>on</sub>	Turn-on Time			1.0	μ <b>s</b>
t <sub>stg</sub>	Storage Time	$I_{C}$ = 2A, $I_{B1}$ = - $I_{B2}$ = 0.2A; R <sub>L</sub> = 5 $\Omega$ ; V <sub>CC</sub> = 10V		2.5	μ <b>S</b>
t <sub>f</sub>	Fall Time			1.0	μ S

### h<sub>FE-2</sub> Classifications

0	Y	G
100-200	160-320	200-400



KSD1691

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3